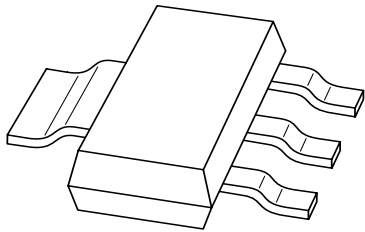


# DATA SHEET



## **BCP51; BCP52; BCP53** PNP medium power transistors

Product specification  
Supersedes data of 2001 Oct 10

2003 Feb 06

**PNP medium power transistors**

**BCP51; BCP52; BCP53**

**FEATURES**

- High collector current
- 1.3 W power dissipation.

**APPLICATIONS**

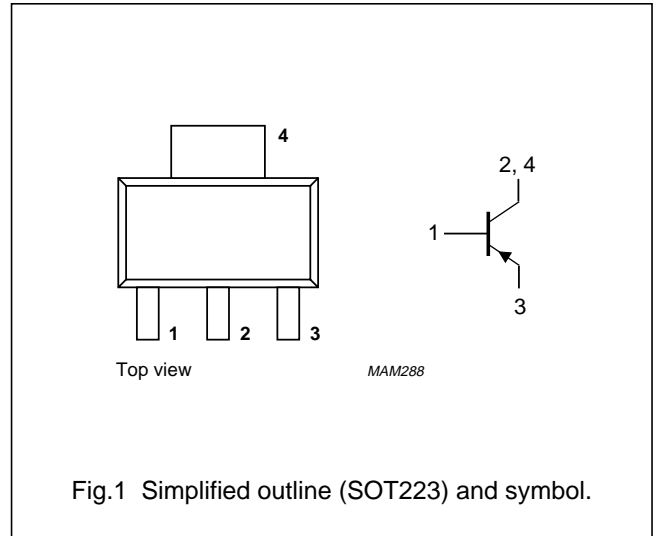
- General purpose medium power DC applications
- Low and medium frequency AC applications
- Peripheral drivers
- Linear voltage regulators and battery chargers.

**DESCRIPTION**

PNP medium power transistor in a SOT223 plastic package. NPN complements: BCP54, BCP55 and BCP56.

**PINNING**

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CE0}$	collector-emitter voltage	-80	V
$I_C$	collector current (DC)	-1	A
$I_{CM}$	peak collector current	-1.5	A

## PNP medium power transistors

## BCP51; BCP52; BCP53

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BCP51		–	–45	V
	BCP52		–	–60	V
	BCP53		–	–100	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BCP51		–	–45	V
	BCP52		–	–60	V
	BCP53		–	–80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–1	A
I <sub>CM</sub>	peak collector current		–	–1.5	A
I <sub>BM</sub>	peak base current		–	–0.2	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	1.3	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Note**

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	95	K/W
R <sub>th j-s</sub>	thermal resistance from junction to soldering point		14	K/W

**Note**

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

PNP medium power transistors

BCP51; BCP52; BCP53

**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -30 V	-	-	-100	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = -30 V; T <sub>j</sub> = 125 °C	-	-	-10	µA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = -5 V	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; see Fig.2 I <sub>C</sub> = -5 mA I <sub>C</sub> = -150 mA I <sub>C</sub> = -500 mA	63	-	-	
			63	-	250	
			40	-	-	
h <sub>FE</sub>	DC current gain BCP51-10; BCP52-10; BCP53-10 BCP51-16; BCP52-16; BCP53-16	I <sub>C</sub> = -150 mA; V <sub>CE</sub> = -2 V; see Fig.2	63	-	160	
			100	-	250	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA	-	-	-0.5	V
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = -500 mA; V <sub>CE</sub> = -2 V	-	-	-1	V
f <sub>T</sub>	transition frequency	I <sub>C</sub> = -10 mA; V <sub>CE</sub> = -5 V; f = 100 MHz	-	115	-	MHz

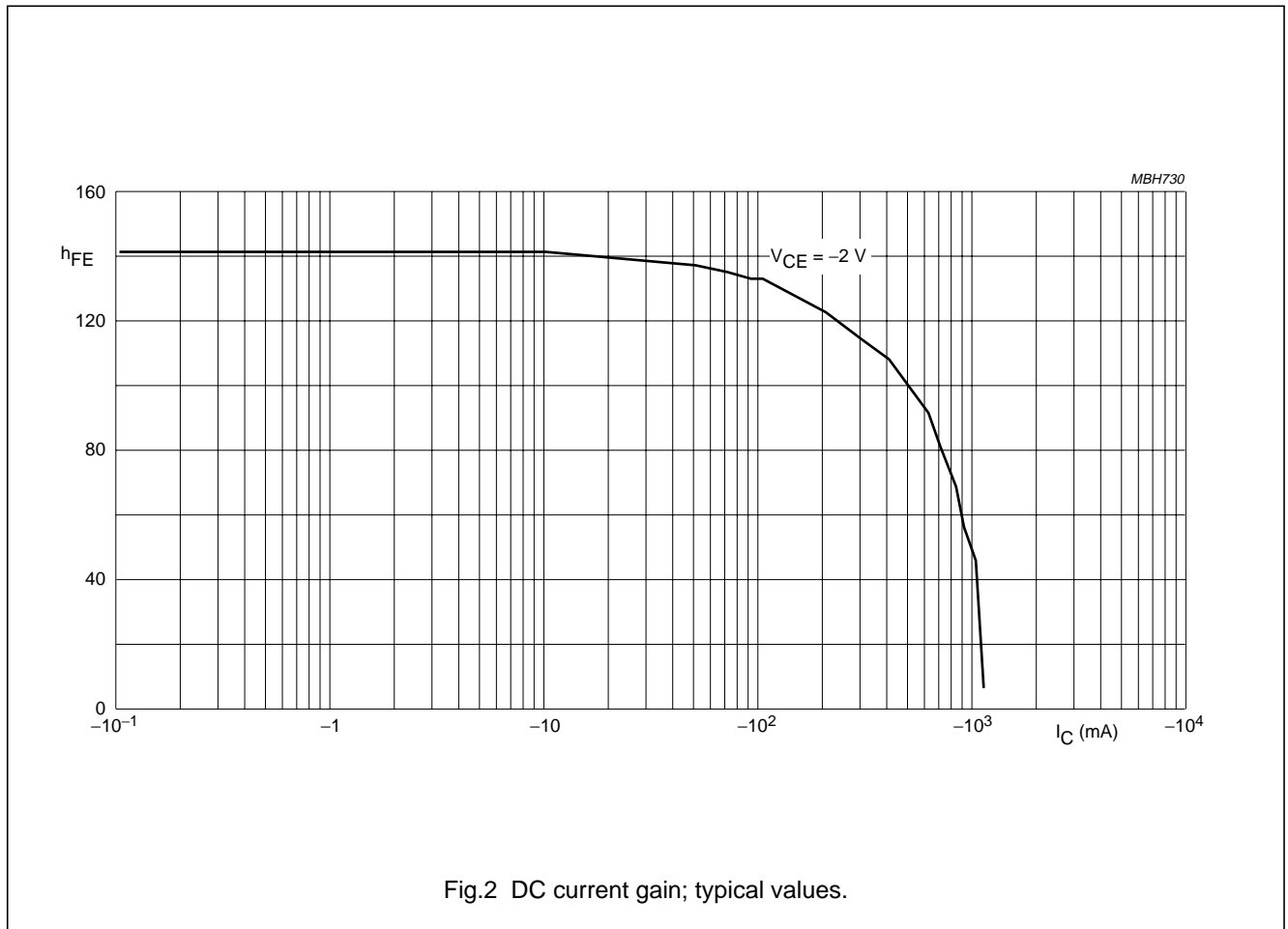


Fig.2 DC current gain; typical values.

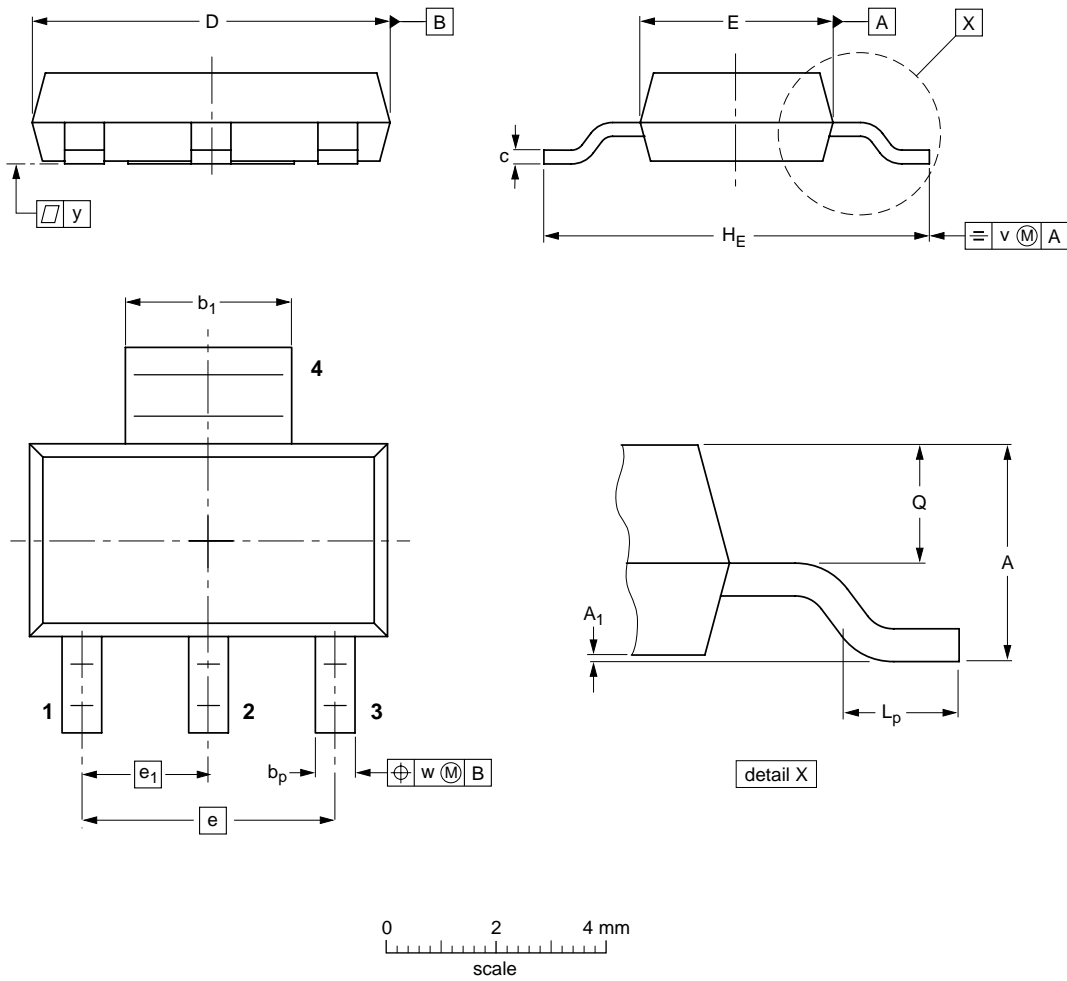
PNP medium power transistors

BCP51; BCP52; BCP53

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			97-02-28 99-09-13

## PNP medium power transistors

## BCP51; BCP52; BCP53

## DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
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PNP medium power transistors

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**NOTES**

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